CRYSTAL GROWTH AND NON LINEAR APPLICATION OF BENZENE SULPHONEAMIDE – AN INSILICO AND INVITRO ANTIBACTERIAL EFFECT AGAINST ESBL (EXTRENDED SPECTRUM OF BETA LACTINIES)

J.Senthilkumaran[1], G.Annamalai[2], R.Shanmugapriya[3], C.Uma[4]

Assistant professor

[1] Department of chemistry,Dhanalakshmi Srinivasan College of arts and science for women, Perambalur, Tamil Nadu

ABSTRACT

Single gems of 4-methyl benzene sulfonamide (4MBS) were effectively developed from fluid arrangement by low temperature arrangement development strategy. The developed gem was described by single gem XRD and powder XRD techniques to acquire the grid boundaries and the diffraction planes of the gem. UV–vis–NIR retention range was utilized to quantify the scope of optical conveyance and optical band hole energy. The optical transmission range was estimated as 250–1200 nm. FTIR ghostly investigations were completed to recognize the presence of useful gatherings in the developed precious stone. The warm conduct of the precious stone was examined from thermo gravimetric investigation (TGA) and differential checking calorim-etry (DSC) study. The nonappearance of SHG was seen by Kurtz and Perry powder procedure. The third request NLO conduct of the material was confirmed by estimating the nonlinear optical properties utilizing Z-filter method and it was discovered that the precious stone is equipped for showing immersion ingestion and self-defo-cusing execution.

Introduction

The compound 4-methyl benzene sulfonamide (CH3C6H4SO2-NH2), a natural material, has a place with centrosymmetric gathering. In spite of the fact that this material was widely concentrated by drug researchers [1–4], it is equipped for producing third request sounds because of centrosymmetric nature. The blend of sweet-smelling amines from 4MBS has been accounted for by Aravind Tapase et al. [5]. Up until this point, no precise investigations of the developed gem are accessible for different portrayal examines. Subsequently, we report in this paper, the development and significant portrayals including third request non-straight optical property of the developed gem. The developed material was first solidified under encompassing conditions utilizing arrangement development strategy. The precious stone was then described utilizing single gem and powder XRD techniques, UV–vis–NIR and FTIR ghostly examinations, dielectric and warm investigations. Kurtz and Perry powder strategy was utilized to test the Second Harmonic Generation (SHG) in the developed precious stone. Since SHG was missing due to centro-symmetric nature, Z-examine strategy was finally utilized to investigate the third request nonlinear coefficients like nonlinear retention coefficient, nonlinear refractive file and powerlessness for certain NLO applications. By and large, third request NLO material are utilized as optical producer,

broadband optical windows, all optical exchanging gadgets, two photon ingestion (TPA) microscopy, photonic gadgets and holography applications. Z-filter procedure, a wrongdoing gle shaft technique for estimating the sign and size of nonlinear refraction, has higher affectability equivalent to the interferometric strategies [6]. The Z check strategy with the spatial pillar bending guideline is a famous technique for contemplating the third request optical non-linearity of the material and it has the upsides of high affectability and straightforwardness [7]. This strategy has likewise been utilized to gauge the third request non-straight opti-cal properties of semiconductors, dielectrics, natural and carbon based materials, fluid precious stones and natural colors [8–12].

Experimental procedure

Single precious stones of 4MBS were developed by moderate dissipation solu-tion development procedure. 1.5 g analar grade (AR) 4-methyl benzene sulfonamide was broken up in methanol to set up an immersed arrangement at room temperature (30 °C). The arrangement was filtered out utilizing a borozil filter paper. The filtered soaked arrangement was covered with tissue paper and pricked with pin to make suit-capable number of openings for gradual dissipation of the solu-tion. The arrangement was then positioned in a consistent temperature shower to keep up the arrangement at a steady temperature (30 °C) with an exactness of ±0.01 °C. At the point when the arrangement starts to dissipate, the immersion continuously achieves supersaturated level prompting nucle-ation and the development of the precious stones. The dissipation rate is con-savaged keeping the arrangement in a consistent temperature shower (without temperature fluctuation) with the end goal that the development rate is controlled to control the quantity of characteristic deformities. The size and virtue of gem were improved by progressive crystalliza-tion measures. Following a time of ten days, straightforward single crys-tals of 4MBS with measurements of 16 4 2 mm3 were gathered. The as-developed single gems of 4MBS are appeared in Fig. 1.

Characterization studies

Single precious stone XRD information of 4MBS were assessed utilizing an automatic X-beam diffractometer (MESSERS ENRAF NONIUS CAD-4, Neth-erlands) with Cu Ka radiation (k = 1.5406 ÅA0). Powder X-beam diffraction range was recorded utilizing a rich seifert diffractometer. The assimilation range of 4MBS precious stone was acquired in the frequency locale of 200–2000 nm utilizing VARIAN CARY 5E model spectrometer. FTIR range of 4MBS was recorded in the scope of 450–4000 cm—1 utilizing IFS 66 V, FTIR spectrometer. Dielectric stud-ies were done at various temperatures utilizing HIOKI 3532 LCR HITESTER in the recurrence range from 50 Hz to 5 MHz. Ther-mal conduct of the material was dissected utilizing NETZSCH-Gerata-bau warm analyser. The procedure created by Kurtz and Perry was utilized to test the presence of second request nonlinearity of the material. Since SHG was missing in the developed gem, Z-filter tech-nique was utilized for investigating the third request non-straight opti-cal conduct of the material.

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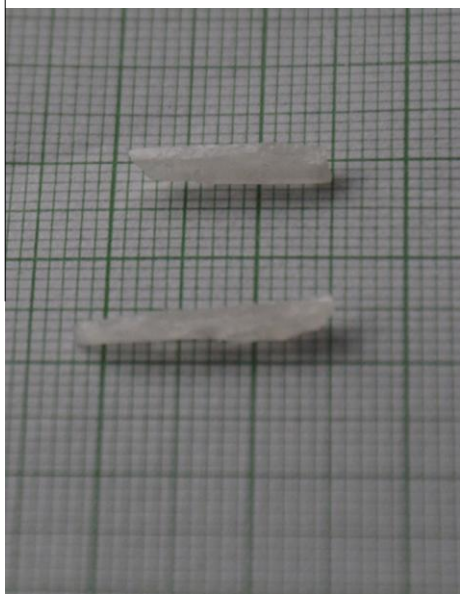
Results and discussion

3.1. XRD analysis

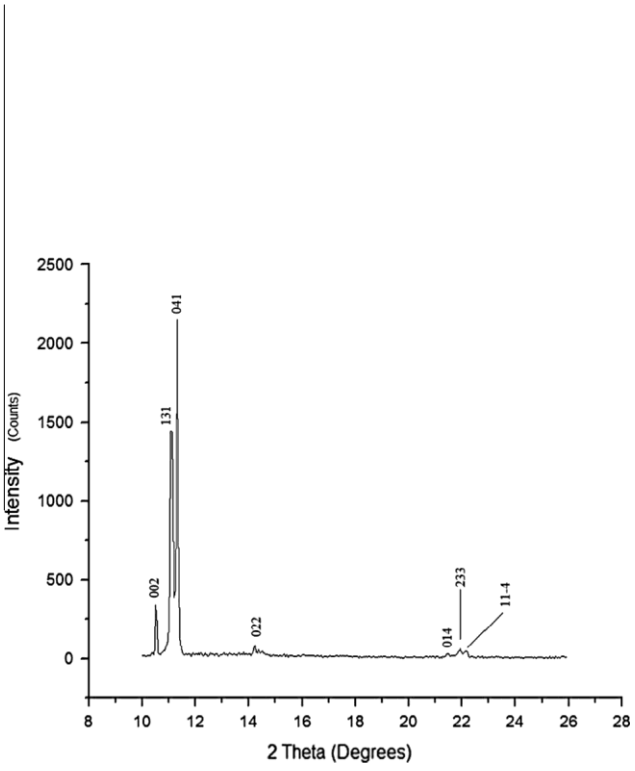


3.1.1 Single crystal XRD

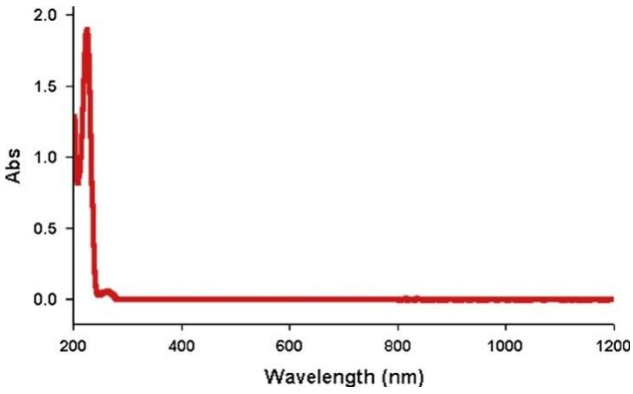
The grown 4MBS crystal was subjected to single crystal X-raydiffraction analysis to confirm the crystallinity and also to estimate attice parameters using ENRAF NONIUS CAD-4 X-RAY diffrac-tometer. From the single XRD data obtained, it is observed that thegrown single crystal belongs to monoclinic system with spacegroup P2 (1)/n,Z= 4. Also, the space group indicates that the crys-tal belongs to centro-symmetric group. The unit cell lattice param-eters determined from single crystal X-ray diffraction analysis dataarea= 6.5884 ÅA0,b= 16.4874 ÅA0andc= 7.7087 ÅA0anda=c=90°andb= 92.459 Å withV= 837.3620 ÅA03. Since the grown material iscento-symmetric in nature, the basic requirement for exhibitingsecond order nonlinear behavior is not fulfilled

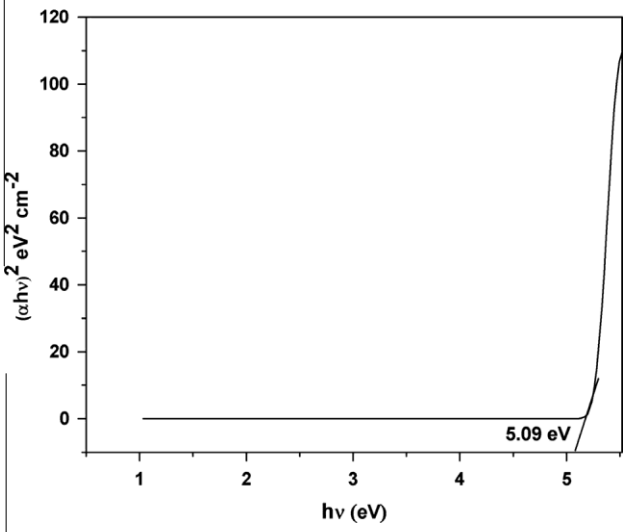
1.2. Powder XRDPowder

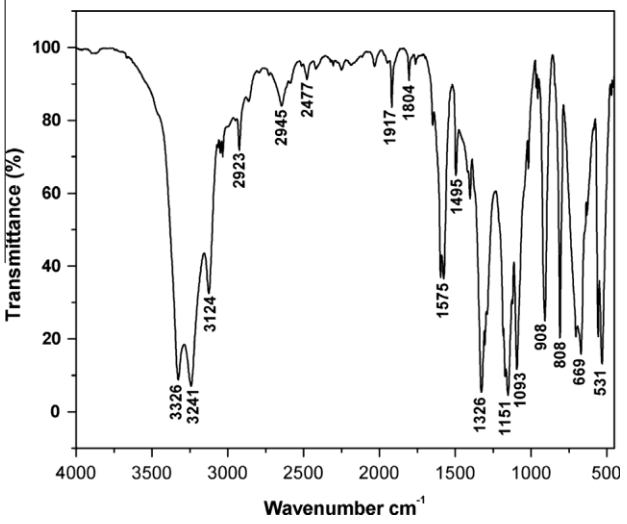
X-ray diffraction analysis was carried out using a richseifert diffractometer with Cu Ka(k= 1.540598 Å) radiation to con-firm the crystal system of the grown 4MBS material. The powdersample was scanned over the range of 10–70°at a scan rate of 1°per minute. The powder XRD spectrum is shown inFig. 2. Usingthe data obtained from powder XRD spectrum, the 'd' values fordifferent 2hcorresponding to the reflecting planes (hkl) of thecrystal were calculated and the lattice parameters were deter-mined using TERROR program. The lattice parameters are pre-sented inTable 1and the results of powder XRD and singlecrystal XRD studies are found to be in good agreement with thereported values [JCPDS NO. 361959]. The powder XRD pattern withthe sharp peaks reflects the good crystalline nature of the grownmaterial 4MBS



3.2. Optical studies







Lattice parameters of 4MBS from powder XRD data.

2*h* (°)	*d* (Å)	Intensity (counts)	*h k l*	Lattice parameters
10.52	3.24345494	342	(0 0 2)	a = 6.597 Å
11.08	3.32866339	1459	(1 3 1)	b = 6.4912 Å
11.32	3.36452076	2150	(0 4 1)	c = 7.7314 Å
14.24	3.77359245	81	(014)	$a = c$ = 90°
21.48	4.63465209	29	(022)	b = 92.503 Å
22.16	4.70744091	47	ð1 1 4Þ	V = 841.1816 Å^3
22.2	4.71168759	39	(233)	

3.2.1.

UV–vis–NIR studyA good optical transmittance is very desirable for any crystal tofind applications in photonics and optoelectronic field. UV–vis–NIRabsorption spectrum is very important for any NLO material to findthe transmission range over a considerable region of wavelength[13].Fig. 3shows the absorption spectrum of the crystal recordedin the range of 200–1200 nm. From the spectrum, it is noticed thatthe absorption of the crystal is considerably low in the wavelengthregion 250–1200 nm. The prominent peaks observed in thespectrum may be due to overtones or the combination bands ofeither stretching or bending vibration in the UV region. From theUV–vis–NIR spectrum, the crystal shows good transparency inthe region 250–1200 nm which includes visible and NIR region.Hence, this transparent nature in the visible and NIR range is adesirable property for inducing polarization and the material can be used for NLO applications. From the spectrum, the UV cutoffwavelength of the material is found to be 225 nm. This indicatesthe maximum absorbance at wavelength 225 nm

FTIR spectral analysis

presents the FTIR range of 4MBS single crystalrecorded in the scope of 450–4000 cm1. The pinnacles correspondingto 3326 cm1and 3241 cm1show the presence of NAH primaryamides and N-subbed amides. Expansive groups with multiplepeaks somewhere in the range of 2850 and 3100 cm1are because of CAH stretchingvibration (both solid and medium). The top at 2645 cm1is a polarization within the sight of outer electric field[17]. Thedielectric steady (er) and dielectric misfortune (e0) were assessed usingthe relations,er¼Cd=e0Aande0¼erDð3ÞwhereCis the capacitance,dis the thickness,e0is the permittivityof free space,Dis the dissemination factor andAis the territory of crosssection of the precious stone. The plot of dielectric consistent (er) versuslog of recurrence (f) is demonstrated inFig. 6. It is seen that the dielec-tric steady has higher qualities in the lower recurrence locale andthen diminishes with increment in recurrence and scopes constantbeyond a specific recurrence of the electric field, since the dipolesdo not follow the exchanging field. The higher qualities oferat low fre-quencies might be because of the presence of all the four polarizationsnamely, space charge, direction, electronic and ionic polarizations[18]and its low an incentive at higher frequencies might be because of the lossof critical polarizations steadily. Henceforth, the huge worth ofdielectric consistent at low frequencies can be credited to the lowerelectrostatic restricting strength which emerges because of space chargepolarization close to the grain limit interfaces. The conductinggrains and the interfaces close to the grain limit in a dielectricmatrix become dipoles because of electrostatic acceptance for the contri-bution towards space charge polarization. The dielectric misfortune wasalso concentrated as a component of recurrence at different temperaturesand is demonstrated inFig. 7. From the plot of dielectric misfortune (Fig. 7), thecurves recommend that the dielectric misfortune unequivocally relies upon the fre-quency of the applied field in the lower district. From the plots, it isalso saw that there is no obvious variety in the qualities ofdielectric consistent and dielectric misfortune regarding temperature.The lower estimations of dielectric misfortune at higher frequencies propose thatthe gem is of acceptable optical quality with least thickness ofdefects and this boundary is of indispensable significance for non-linearoptical applications.

3.4 Dielectric studie

The dielectric attributes of the material are significant toestablish the dielectric idea of the material. The dielectric prop-erties are connected with the electro-optic properties of the growncrystals[16]. The dielectric investigation of the developed gem was carriedout utilizing HIOKI 3532 LCR HITESTER for the frequencies from 50 Hzto 5 MHz at the temperatures 313 K, 323 K, 333 K and 343 Krespectively. Basically, the dielectric consistent is the measure o the gem is given as 135.5°C utilizing TGA bend. This is confirmedby the sharp endothermic pinnacle of DSC bend at a similar temper-ature. The vanishing of water particles is steady between135.5°C and 225°C. The deterioration of the material is promi-nently showed by the sharp weight reduction at the temperature225°C which is spoken to by the expansive exothermic top in theDSC bend. The disintegration in the material is because of quick evap-speech of caught water atoms and different fumes, for example, CO2,H2, and S from the developed material. It is seen that the decom-position measure is finished at the temperature 299.1°C and thisis affirmed by the sharp endothermic pinnacle of the DSC bend. After300°C the remaining mass is discovered to be negative. This implies that asample had modest quantity of buildup stayed after the comple-tion of the vanishing cycle, it would prompt stage changesindicated by various endothermic pinnacles of DSC bend. Therefore,it is inferred that the materi al is thermally steady up to141.1°C without weight reduction

Conclusion

Great quality single gems of 4MBS were effectively grownusing moderate vanishing method at surrounding conditions. SingleXRD investigation was utilized to recognize the precious stone framework and spacegroup which was affirmed by powder XRD examination. The opticalabsorption concentrates from UV–vis–NIR range show that thegrown gems have wide straightforward reach in the district 250–1200 nm with 225 nm as the lower cutoff frequency. FTIR spec-tral study was done to distinguish the sub-atomic vibrations ofvarious utilitarian gatherings present in the gem. The warm stud-ies TGA and DSC were investigated to comprehend the warm stabilityof the developed material. Dielectric nature of the material was estab-lished from dielectric considers. The nonattendance of SHG affirmed byKurtz and Perry procedure predicts the centrosymmetric natureof the translucent material. The third request nonliner coefficientswere assessed usingZscan strategy and these coefficients arefound to display self-defocusing impact. Subsequently, 4MBS is an excellentthird request NLO material which can discover applications in optoelec-tronic, photonics and holographic applications.

REFERENCES

[1] H. Meng, M.Y. Li, W.L. Zhu, Nan Fang Yi Ke Da Xue Xue Bao, PMID:19460736[PubMed - indexed for MEDLINE, 29 (2009), pp. 1024–1025.

[2] T. Wang, Y. Li, M. Liu, Practice J. Cancer 19 (2004) 1–4.

[3] Aravind Tapase, D. Narayan, D. Shinde, Devanand Shinde, Bull. Environ. Pharmacol. Life. Sci. 1 (10) (2012) 50–54.

[4] M. Sheik-Bahae, A.A. Said, E.W. Van Stryland, Opt. Lett. 14 (1989) 955–957.

[5] Sheik-Bahe, A.A. Said, T.H. Wei, D.J. Hagan, E.W. Van Stryland, IEEE J. Quantum Electron. 26 (1990) 760–769.

[8] T.D. Krauss, F.W. Wise, Appl. Phys. Lett. 65 (1994) 1739–1741.

[9] R. Rangel-Roja, T. Kosa, E. Hajito, P.J.S. Ewen, A.E. Owen, A.K. Kar, B.S. Whereet, Opt. Commun. 109 (1994) 145–150.

[10] T.H. Wei, D.J. Hagan, M.J. Sence, E.W. Van Stryland, J.W. Perry, D.R. Coulter, Appl. Phys. B54 (1992) 46–51.

[11] V. Natarajan, T. Sivanesan, S. Pandi, Indian J. Sci. Technol. 3 (8) (2010) 897–899.

[12] Umakanta Tripathy, R. Justin Rajesh, Prem B. Bisht, A. Subramahamanyam, Proc. Indian Acad. Sci. (Chem. Sci.) 114 (6) (2002) 557–564.

[13] V. Krishnakumar, R. Nagalakshmi, Acta A 61 (2005) 499–507.

[14] J. Tauc, Amorphous and Liquid Semiconductor, Plenum Press, New York, 1974. p. 159.

[15] D.D.O. Eya, A.J. Ekpunobi, C.E. Okeke, Acad. Open Internet J. 17 (2006).

[16] S. Goma, C.M. Padma, C.K. Mahadevan, Mater. Lett. 60 (2006) 3701–3705.

[17] P.S. Aithal, H.S. Nagaraja, P. Mohan Rao, D.K. Avasti, A. Sarma, Vacuum 48 (1997) 991–994.

[18] B.K. Singh, N. Sinha, N. Singh, K. Kumar, M.K. Gupta, BinayKumar, J. Phys. Chem. Solids 71 (2010) 1774–1779.

[19] S.K. Kurtz, T.T. Perry, J. Appl. Phys. 39 (1968) 798–813.

[20] V. Natarajan, T. Sivanesan, S. Pandi, Indian J. Sci. Technol. 3 (8) (2010). ISSN: 0974-6846..

[21] R. Ashok Kumar, R. Ezhil Vizhi, N. Vijayan, G. Bhagavannarayan, D. Rajan Babu, J. Pure Appl. Ind. Phys. 1 (1) (2010) 61–67.